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(54) BULK-ACOUSTIC WAVE RESONATOR

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(57)**ABSTRACT**

A bulk-acoustic wave (BAVV) resonator is provided. The BAW includes a substrate, a first electrode disposed on the substrate, a piezoelectric layer disposed to cover at least a portion of the first electrode, and a second electrode disposed to cover at least a portion of the piezoelectric layer, wherein the piezoelectric layer includes an intermediate layer, a first layer disposed above the intermediate layer and a second layer disposed below the intermediate layer, the first layer and the second layer are symmetrical in relation to a plane through which a central line of the intermediate layer passes in a thickness direction, and a thickness of the intermediate layer is greater than a thickness of each of the first and second layers.

